

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	0	"134".ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 15:14
S2	38059	"134"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 15:15
S3	5010	S2 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 15:15
S4	2754	S3 and particle	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 15:15
S5	15224	S2 and partic\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 15:16
S6	232	S5 and (electron adj microscope)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 15:17
S7	86	S6 and (Ti or titanium or TiN or (titanium adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 15:48
S8	0	S7 and HNO	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 15:48
S9	18	S7 and (nitric adj acid)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 15:48
S10	0	S9 and phos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 15:48

S11	6	S9 and acetic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 16:03
S12	35566	phosphoric and nitric and acetic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 13:23
S13	1620	S12 and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 16:04
S14	996	S13 and ((Ti or titanium or Tin) or titanium adj nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 16:05
S15	570	S14 and removal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 16:05
S16	476	S15 and partic\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 16:06
S17	220	S16 and (barrier or liner)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 16:16
S18	4324	forming adj barrier adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 16:17
S19	1280	S18 and Ti	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 16:17
S20	2210	S18 and (Ti or titanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 16:19

S21	136	((forming adj barrier adj layer) and (Ti or titanium)).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 16:33
S22	1	S21 and (conductor near (poly or polysilicon or silicide or metal))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 16:31
S23	2	((forming adj barrier adj layer) and (Ti or titanium)) and particles and rework	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 16:34
S24	3193	(Ti or titanium) near (particle or paticulate or residual or contaminant or residue) and (rework or removal or etch or remove)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 16:35
S25	1079	(Ti or titanium) adj (particle or paticulate or residual or contaminant or residue) and (rework or removal or etch or remove)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 16:36
S26	31	((Ti or titanium) adj (particle or paticulate or residual or contaminant or residue) and (rework or removal or etch or remove)).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 16:51
S27	118598	(remove (Ti or titanium) near (substrate or layer)) and barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 16:53
S28	27	(remove adj (Ti or titanium) near (substrate or layer)) and barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 16:55
S29	77	(remove adj (Ti or titanium)) near (substrate or layer or barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 16:57
S30	0	(wet adj etch) near (remove adj (Ti or titanium)) near (substrate or layer or barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 16:57

S31	9	(wet adj etch) and (remove adj (Ti or titanium)) near (substrate or layer or barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 16:59
S32	44	(remove adj (Ti or titanium)) adj particle	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 17:01
S33	5	S32 and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 17:00
S34	50	(remove adj (Ti or titanium)) adj (particle or residue or residual or contaminant)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 17:02
S35	5	S34 and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 17:02
S36	50	remove near (Ti or titanium) near (particle or residue or residual or contaminant)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 17:03
S37	0	rework near ((Ti or titanium) near (particle or residue or residual or contaminant))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 17:03
S38	98	(rework or remove) near ((Ti or titanium) near (particle or residue or residual or contaminant))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 17:04
S39	26	S38 and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 17:09
S40	5	((sulfuric or H ₂ SO ₄ or sulphate or phated or SO ₄ or "H. _{sub.2} SO. _{sub.4} " or "H. _{sub.x} SO. _{sub.x} " or "H. _{sub.n} SO. _{sub.n} " or "H. _{sub.x} SO. _{sub.n} " or "H. _{sub.n} SO. _{sub.x} "") near rinse) and (Titanium or Ti)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 17:15

S41	8	((sulfuric or H ₂ SO ₄ or sulphate or phated or SO ₄ or "H.sub.2SO.sub.4" or "H.sub.xSO.sub.x" or "H.sub.nSO.sub.n" or "H.sub.xSO.sub.n" or "H.sub.nSO.sub.x") near rinse) and (corrosion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 17:16
S42	0	((sulfuric or H ₂ SO ₄ or sulphate or phated or SO ₄ or "H.sub.2SO.sub.4" or "H.sub.xSO.sub.x" or "H.sub.nSO.sub.n" or "H.sub.xSO.sub.n" or "H.sub.nSO.sub.x") near rinse) and clean and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 17:17
S43	3084	sulfuric and clean and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 17:17
S44	6	sulfuric adj clean and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 17:19
S45	4	(sulfuric adj acid adj clean) and (Ti or titanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 17:22
S46	35	sulfuric adj acid adj clean	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/23 17:22
S47	270	wafer and reclaim and process	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:20
S48	279	wafer and reclaim and (process or method)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:22
S49	50	S48 and (Titanium or Ti)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:23
S50	0	S49 and H ₃ PO ₄ and HNO ₃ and CH ₃ COOH	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:21

S51	14	(wafer and reclaim and (process or method)).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:22
S52	0	S51 and (titanium or Ti)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:22
S53	2146395	(particle or residual or residue or contaminant)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:24
S54	104490	(Titanium or Ti) and (TiN or (titanium adj nitide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:25
S55	2214123	detection or (electrical adj characteristics) or (electron adj microscope) or map\$4 or scan\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:38
S56	233664	exam or examination	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:28
S60	102796	S56 and S55	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:31
S61	48618	S60 and S53	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:32
S62	360920	S55 and S53	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:32
S63	21267	S62 and S54	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:32

S64	2403	S61 and S54	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:33
S65	21267	S53 and S55 and S54	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:34
S66	4013	S65 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:35
S67	1309	S66 and (electron adj microscop\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:35
S68	3495	S66 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:36
S69	860	S67 and particles	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:36
S70	860	S67 and particle	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:38
S71	48	S67 and ((detect\$\$ or find or map\$4 or scan\$4) near particle)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:40
S72	2913	(particle adj (recogni\$4 or detect\$4 or find or scan or identifcation)).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:41
S73	2044	(particle adj (recogni\$4 or detect\$4 or find or scan or identifcation)) and system.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:43

S74	1530881	S73 and wafer or semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:42
S75	743	S73 and (wafer or semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:42
S76	28	S75 and S54	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:42
S77	89	(particle adj (recogni\$4 or detect\$4 or find or scan or identifcation)) and (electron adj microscope).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:46
S78	25	(particle adj detection) and (wafer adj fabrication)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 12:17
S79	0	2003/0178391	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:54
S80	0	"0178391" and Johnson	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:54
S81	0	3003/099637	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:56
S82	1	10/454023	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:57
S83	1	"10421293"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 10:57

S84	25	(particle adj detection) and (wafer adj fabrication)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 12:29
S86	644	particle adj inspection	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 12:29
S87	4870014	S86 and after process	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 12:30
S88	76	S86 and ((post or after) near process\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 11:37
S89	27	S88 and electron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 12:37
S90	17	S88 and particle.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 12:38
S91	4	S90 and electron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 12:51
S92	74	(rework adj wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 12:51
S93	585	(remove adj barrier adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 12:52
S94	0	S93 and S92	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 12:51

S95	198	S93 and (Ti or titanuim)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 12:52
S96	7	La13 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 12:52
S97	122	S95 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 12:53
S98	52	S97 and defect	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 13:01
S99	0	(titanium or Ti) near electrical adj defect	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 13:02
S100	137	(titanium or Ti) and electrical adj defect	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 13:02
S101	35	(titanium or Ti) and killer adj defect	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 13:15
S102	19	wet adj etch near titanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 13:20
S103	10	"5,936,306"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 13:24
S104	8	wet adj etch adj metal adj layers	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 13:25

S10 5	0	wet adj etch adj metal near (phosphoric or H ₂ PO ₄)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 13:26
S10 6	0	wet adj etch adj metal and (phosphoric or H ₂ PO ₄)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 13:26
S10 7	0	wet adj etch near metal and (phosphoric or H ₂ PO ₄)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 13:26
S10 8	3	wet adj etch and metal and (phosphoric or H ₂ PO ₄)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 13:29
S10 9	0	wet adj etch and titanium and (phosphoric or H ₂ PO ₄)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 13:42
S11 0	36	(phosphoric or H ₂ PO ₄) and (nitric or HNO ₃) and (acetic or CH ₃ COOH)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:00
S11 1	5	etch adj rework and wafers	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:08
S11 2	258	etch and rework and titanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:08
S11 3	756	rework and titanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:09
S11 4	0	rework near titanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:08

S11 5	14	titanium adj nitride and H3PO4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:16
S11 6	1590837	barrier removal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:17
S11 7	309	barrier adj removal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:17
S11 8	10	etch adj barrier adj removal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:22
S11 9	322110	sulfuric rinse	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:22
S12 0	1	sulfuric adj rinse	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:23
S12 1	787025	sulfuric clean	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:23
S12 2	6	sulfuric adj clean	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:29
S12 3	2216	Schottky adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:33
S12 4	41	S123 and Ti and TiN	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:30

S12 5	11	S124 and schottky.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:30
S12 6	4	S123 and rework	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:37
S12 7	285	barrier adj layer and rework	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:37
S12 8	178	S127 and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:39
S12 9	101	S128 and titanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:51
S13 0	4	wet adj etch adj barrier adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:53
S13 1	2162	wet adj etch and barrier adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:53
S13 2	1248	S131 and titanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:53
S13 3	805	S132 and titanium adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 14:59
S13 4	0	wet near remove near (barrier adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 15:00

S13 5	288	acid and remove near (barrier adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 15:00
S13 6	680881	S135 an(ti or titanium)acid and remove near (barrier adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 15:01
S13 7	204	S135 and (ti or titanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 15:01
S13 8	72	S137 not CMP	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 15:39
S13 9	4	schottky adj gate and two adj level adj metal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 15:43
S14 0	3	"6558739".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 15:51
S14 1	2	"5,338,975".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 15:59
S14 2	121	three adj level adj metal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 15:59
S14 3	470	multi adj level adj metal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 15:59
S14 4	187	S143 and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 15:59

S14 5	81	S144 and barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 16:00
S14 6	68	S145 and (Titanium or Ti)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 16:00
S14 7	46	S146 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/24 16:00
S14 8	2	"5338975".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 07:33
S14 9	189	(barrier adj layer) and (plug adj hole)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 07:34
S15 0	111	S149 and (ti or TiN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 07:44
S15 1	80	S150 and ((chemical adj vapor adj deposition) or CVD)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 11:40
S15 2	450	(instection or examination) and rework	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 07:58
S15 3	114	S152 and wafers	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 07:59
S15 4	66	S153 and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 07:59

S15 5	0	S154 and scrub	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 07:59
S15 6	0	S154 and sonics	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 07:59
S15 7	0	S154 and ultraonics	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 08:00
S15 8	0	S154 and meganics	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 08:01
S15 9	2	"5,338,975".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 08:45
S16 0	88	(contaminant or particle or (killer adj defect)) near barrier adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 08:46
S16 1	7	S160 and detect	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 08:47
S16 2	0	S161 and (examine or inspect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 08:47
S16 3	59	semiconductor adj inspection adj methods	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 08:48
S16 4	9	S163 and electron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 09:39

S16 5	2	"4,822,753".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 09:44
S16 6	784	(etch adj (barrier or titanium)) and solution	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 09:45
S16 7	643	S166 and barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 09:45
S16 8	211	S167 and (wet adj etch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 09:45
S16 9	112	S168 and titanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 09:46
S17 0	131	S168 and interconnect	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 09:46
S17 1	86	S169 and interconnect	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 09:47
S17 2	14	S171 and sulfuric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 09:49
S17 3	11	S171 and (phosphoric or H3PO4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 09:50
S17 4	2	"5514622".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 11:37

S17 5	189	(barrier adj layer) and (plug adj hole)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 12:34
S17 6	111	S175 and (ti or TiN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 11:40
S17 7	80	S176 and ((chemical adj vapor adj deposition) or CvD)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 11:40
S17 8	29	S177 and polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 12:00
S17 9	5	S178 and Ti/TiN	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 12:32
S18 0	92840	S179 ans silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 12:32
S18 1	3	S179 and silicide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 12:32
S18 2	10	S175 and silicide near formation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 13:06
S18 3	2	"5633111".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 13:06
S18 4	187570	(phosphoric adj acid) or H ₃ PO ₄ or "H. _{sub} .3PO. _{sub} .4" or "H. _{sub} .xPO. _{sub} .x" or "H. _{sub} .nPO. _{sub} .n" or "H. _{sub} .xPO. _{sub} .n" or "H. _{sub} .nPO. _{sub} .x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 13:35

S18 5	100101	(Nitric adj acid) or (HNO3 or HNOx or HNO _n or HNO _{subx} or HNO _{subn} or "HNO.subx" or "HNO.subn" or "HNO.sub.x" or "HNO.sub.n")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 13:35
S18 6	260718	(acetic adj acid) or (CH ₃ COOH or CH ₃ COOH _{Chsub3} COOH or "CH _{sub} 3.COOH" or CH _x COOH or "CH _{sub} x.COOH" or CH _{subx} COOH)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 13:38
S18 7	3681296	water or aqueous or H ₂ O or (H ₂ O or H _x O or H _n O or "H _{sub} 2O" or "H _{subx} O" or "H _{subn} O" or "H _{sub} 2.O" or "H _{sub} x.O" or "H _{sub} n.O")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 13:39
S18 8	21249	S184 and S185 and S186 and S187	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 13:39
S18 9	130	S184 near S185 near S186 near S187	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 13:39
S19 0	1169	S188 and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 13:40
S19 1	65	S189 and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 13:40
S19 2	57	S191 and metal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 13:40
S19 3	30	S192 and titanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 15:59
S19 4	4	"6362027".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 17:04

S19 5	2	"5,598,284".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 15:59
S19 6	5	"6,613,614".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/27 17:05
S19 7	5	"6,613,614".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:22
S19 8	2	"6447604".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:23
S19 9	4571	(TiN or titanium nitride) near barrier	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/06 14:35
S20 0	0	colbalt near substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 14:36
S20 1	771	cobalt near substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 14:43
S20 3	1460	(TiN or (titanium adj nitride)) near barrier	USPAT	OR	ON	2005/12/06 14:48
S20 4	4	(TiN or (titanium adj nitride)) near colbalt	USPAT	OR	ON	2005/12/06 14:42
S20 5	731	(TiN or (titanium adj nitride)) near Cvd	USPAT	OR	OFF	2005/12/06 14:43
S20 6	5	S201 and S203	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 14:44

S20 7	3598488	plug or via	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 14:44
S20 8	4	S206 and S207	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 14:46
S20 9	118	cobalt near (plug or via)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 14:46
S21 0	18	(cobalt adj silicide) near (plug or via)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 14:47
S21 1	1602	(TiN or (titanium adj nitride)) near (barrier or liner)	USPAT	OR	ON	2005/12/06 14:49
S21 4	220342	(Ti or TiN) or (titanium or (titanium adj nitride)) near (barrier or liner)	USPAT	OR	ON	2005/12/06 14:58
S21 5	4	S210 and S214	USPAT	OR	ON	2005/12/06 14:50
S21 6	37952	S214 and cobalt	USPAT	OR	ON	2005/12/06 14:56
S21 7	219913	(Ti or TiN) or (titanium or (titanium adj nitride)) near (barrier or liner) near on near cobalt	USPAT	OR	ON	2005/12/06 14:58
S21 8	220037	(Ti or TiN) or (titanium or (titanium adj nitride)) near (liner or glue)	USPAT	OR	ON	2005/12/06 15:01
S22 0	37908	S218 and cobalt	USPAT	OR	ON	2005/12/06 14:59
S22 1	12548	S220 and deposition	USPAT	OR	ON	2005/12/06 15:00
S22 2	2689	S221 and etch	USPAT	OR	ON	2005/12/06 15:00
S22 3	1539	S222 and cvd	USPAT	OR	ON	2005/12/06 15:00
S22 6	1118	S223 and (plug or via)	USPAT	OR	ON	2005/12/06 15:00

S22 8	219925	(Ti or TiN) or (titanium or (titanium adj nitride)) near (liner or glue) near (plug or via)	USPAT	OR	ON	2005/12/06 15:09
S22 9	18	cobalt near bottom	USPAT	OR	ON	2005/12/06 15:01
S23 0	7	S228 and S229	USPAT	OR	ON	2005/12/06 15:02
S23 1	1347531	cobalt near under (via or plug)	USPAT	OR	ON	2005/12/06 15:03
S23 8	843	deposit near (Ti or TiN) or (titanium or (titanium adj nitride)) near (liner or glue) near (plug or via)	USPAT	OR	ON	2005/12/06 15:20
S23 9	5	S238 and (over near cobalt)	USPAT	OR	ON	2005/12/06 15:10
S24 0	219913	(Ti or TiN) or (titanium or (titanium adj nitride)) near (liner or glue) near (plug or via).ti.	USPAT	OR	ON	2005/12/06 15:20
S24 1	2592	((Ti or TiN) or (titanium or (titanium adj nitride)) near (liner or glue) near (plug or via)).ti.	USPAT	OR	ON	2005/12/06 15:20
S24 2	3	(deposit near (Ti or TiN) or (titanium or (titanium adj nitride)) near (liner or glue) near (plug or via)).ti.	USPAT	OR	ON	2005/12/06 15:21
S24 3	171	(Cvd same (Ti or TiN) or (titanium or (titanium adj nitride)) near (liner)).ab.	USPAT	OR	ON	2005/12/06 15:22
S24 4	21	S243 and (barrier.ti.)	USPAT	OR	ON	2005/12/06 15:25
S24 5	0	S244 and cobalt	USPAT	OR	ON	2005/12/06 15:23
S24 6	0	(ti near glue) and (tin near liner) and cobalt	USPAT	OR	ON	2005/12/06 15:26
S24 7	0	((ti near glue) and (tin near liner)).ab.	USPAT	OR	ON	2005/12/06 15:26
S24 8	0	((ti near (glue adj layer)) and (tin near liner)).ab.	USPAT	OR	ON	2005/12/06 15:26
S24 9	1	((ti near (glue adj layer)) and (tin near liner))	USPAT	OR	ON	2005/12/06 15:28
S25 1	1	((ti near (seed adj layer)) and (tin near liner))	USPAT	OR	ON	2005/12/06 15:30
S25 2	2	glue near layer near Ti near TiN near barrier near layer	USPAT	OR	ON	2005/12/06 15:37
S25 7	0	cvd near form near ti near tin	USPAT	OR	OFF	2005/12/06 15:38
S25 8	0	cvd near form near (ti and tin)	USPAT	OR	OFF	2005/12/06 15:39

S25 9	716	cvd same form same (ti and tin)	USPAT	OR	OFF	2005/12/06 15:39
S26 0	102	S259 and cobalt	USPAT	OR	OFF	2005/12/06 16:43
S26 1	0	rework near (Ti and TiN)	USPAT	OR	OFF	2005/12/06 16:44
S26 2	0	rework near (Titanium)	USPAT	OR	OFF	2005/12/06 16:44
S26 3	32	rework same (Titanium)	USPAT	OR	OFF	2005/12/06 16:48
S26 4	3	rework same (Titanium adj Nitride)	USPAT	OR	OFF	2005/12/06 16:44
S26 5	3	S263 and S264	USPAT	OR	OFF	2005/12/06 16:44
S26 6	3	rework same (Ti and TiN)	USPAT	OR	OFF	2005/12/06 17:21